

Abstract Submitted
for the GEC14 Meeting of
The American Physical Society

Transport Properties of Negative Ions in HBr Plasmas

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[1] K. Denpoh and K. Nanbu, J. Vac. Sci. Technol. A (1998) 16 1201-1206.

[2] R. L. Champion, L.D. Doverspike, M.S. Huq, D. Scott and Y. Wang, J.Chem.Phys. (1988) 88(9) 5475.

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Date submitted: 13 Jun 2014

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